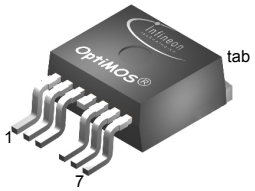
MOSFET

OptiMOS™ 5 Power-Transistor, 100 V

D²-PAK 7pin



Features

- Ideal for high frequency switching and sync. rec.
- Excellent gate charge x $R_{DS(on)}$ product (FOM)
- Very low on-resistance $R_{DS(on)}$
- N-channel, normal level
- 100% avalanche tested
- Pb-free plating; RoHS compliant
- Qualified according to JEDEC[1)] for target applications
- Halogen-free according to IEC61249-2-21

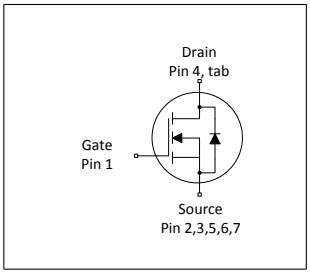


Table 1 Key Performance Parameters

Parameter	Value	Unit
V_{DS}	100	V
$R_{DS(on),max}$	2.4	mΩ
I_D	221	A
Q_{oss}	142	nC
Q_G(0V..10V)	111	nC

Type / Ordering Code	Package	Marking	Related Links
IPB024N10N5	PG-TO263-7	024N10N5	-

[1)] J-STD20 and JESD22

Table of Contents

1 Maximum ratings

at T_A=25 °C, unless otherwise specified

Table 2 Maximum ratings

Parameter	Symbol	Values			Unit	Note / Test Condition
		Min.	Typ.	Max.		
Continuous drain current[1)]	I_D	- -	- -	221 169	A	T_C=25 °C T_C=100 °C
Pulsed drain current[2)]	$I_{D,pulse}$	-	-	884	A	T_C=25 °C
Avalanche energy, single pulse	E_{AS}	-	-	502	mJ	I_D=100 A, R_{GS}=25 Ω
Gate source voltage	V_{GS}	-20	-	20	V	-
Power dissipation	P_{tot}	-	-	250	W	T_C=25 °C
Operating and storage temperature	T_j, T_{stg}	-55	-	175	°C	IEC climatic category; DIN IEC 68-1: 55/175/56

2 Thermal characteristics

Table 3 Thermal characteristics

Parameter	Symbol	Values			Unit	Note / Test Condition
		Min.	Typ.	Max.		
Thermal resistance, junction - case	R_{thJC}	-	0.4	0.6	K/W	-
Thermal resistance, junction - ambient, minimal footprint	R_{thJA}	-	-	62	K/W	-
Thermal resistance, junction - ambient, 6 cm^2 cooling area[3)]	R_{thJA}	-	-	40	K/W	-
Soldering temperature and reflow soldering is allowed	T_{sold}	-	-	260	°C	reflow MSL1

[1)] Rating refers to the product only with datasheet specified absolute maximum values, maintaining case temperature as specified. For other case temperatures please refer to Diagram 2. De-rating will be required based on the actual environmental conditions.
[2)] see Diagram 3
[3)] Device on 40 mm x 40 mm x 1.5 mm epoxy PCB FR4 with 6 cm^2 (one layer, 70 µm thick) copper area for drain connection. PCB is vertical in still air.

3 Electrical characteristics

at T_j=25 °C, unless otherwise specified

Table 4 Static characteristics

Parameter	Symbol	Values			Unit	Note / Test Condition
		Min.	Typ.	Max.		
Drain-source breakdown voltage	$V_{(BR)DSS}$	100	-	-	V	V_{GS}=0 V, I_D=1 mA
Gate threshold voltage	$V_{GS(th)}$	2.2	3.0	3.8	V	V_{DS}=V_{GS}, I_D=183 µA
Zero gate voltage drain current	I_{DSS}	- -	0.1 10	5 100	µA	V_{DS}=100 V, V_{GS}=0 V, T_j=25 °C V_{DS}=100 V, V_{GS}=0 V, T_j=125 °C
Gate-source leakage current	I_{GSS}	-	1	100	nA	V_{GS}=20 V, V_{DS}=0 V
Drain-source on-state resistance	$R_{DS(on)}$	- -	2.0 2.4	2.4 3.2	mΩ	V_{GS}=10 V, I_D=90 A V_{GS}=6 V, I_D=45 A
Gate resistance[1)]	R_G	-	1.2	1.8	Ω	-
Transconductance	g_{fs}	105	210	-	S	|V_{DS}|>2|I_D|$R_{DS(on)max}$, I_D=90 A

Table 5 Dynamic characteristics[1)]

Parameter	Symbol	Values			Unit	Note / Test Condition
		Min.	Typ.	Max.		
Input capacitance	C_{iss}	-	7870	10200	pF	V_{GS}=0 V, V_{DS}=50 V, f=1 MHz
Output capacitance	C_{oss}	-	1200	1560	pF	V_{GS}=0 V, V_{DS}=50 V, f=1 MHz
Reverse transfer capacitance	C_{rss}	-	53	93	pF	V_{GS}=0 V, V_{DS}=50 V, f=1 MHz
Turn-on delay time	$t_{d(on)}$	-	20	-	ns	V_{DD}=50 V, V_{GS}=10 V, I_D=90 A, $R_{G,ext}$=1.6 Ω
Rise time	t_r	-	12	-	ns	V_{DD}=50 V, V_{GS}=10 V, I_D=90 A, $R_{G,ext}$=1.6 Ω
Turn-off delay time	$t_{d(off)}$	-	42	-	ns	V_{DD}=50 V, V_{GS}=10 V, I_D=90 A, $R_{G,ext}$=1.6 Ω
Fall time	t_f	-	13	-	ns	V_{DD}=50 V, V_{GS}=10 V, I_D=90 A, $R_{G,ext}$=1.6 Ω

Table 6 Gate charge characteristics[2)]

Parameter	Symbol	Values			Unit	Note / Test Condition
		Min.	Typ.	Max.		
Gate to source charge	Q_{gs}	-	36	-	nC	V_{DD}=50 V, I_D=90 A, V_{GS}=0 to 10 V
Gate to drain charge[1)]	Q_{gd}	-	23	34	nC	V_{DD}=50 V, I_D=90 A, V_{GS}=0 to 10 V
Switching charge	Q_{sw}	-	35	-	nC	V_{DD}=50 V, I_D=90 A, V_{GS}=0 to 10 V
Gate charge total[1)]	Q_g	-	111	138	nC	V_{DD}=50 V, I_D=90 A, V_{GS}=0 to 10 V
Gate plateau voltage	$V_{plateau}$	-	4.6	-	V	V_{DD}=50 V, I_D=90 A, V_{GS}=0 to 10 V
Output charge[1)]	Q_{oss}	-	142	188	nC	V_{DD}=50 V, V_{GS}=0 V

[1)] Defined by design. Not subject to production test.
[2)] See ″Gate charge waveforms″ for parameter definition

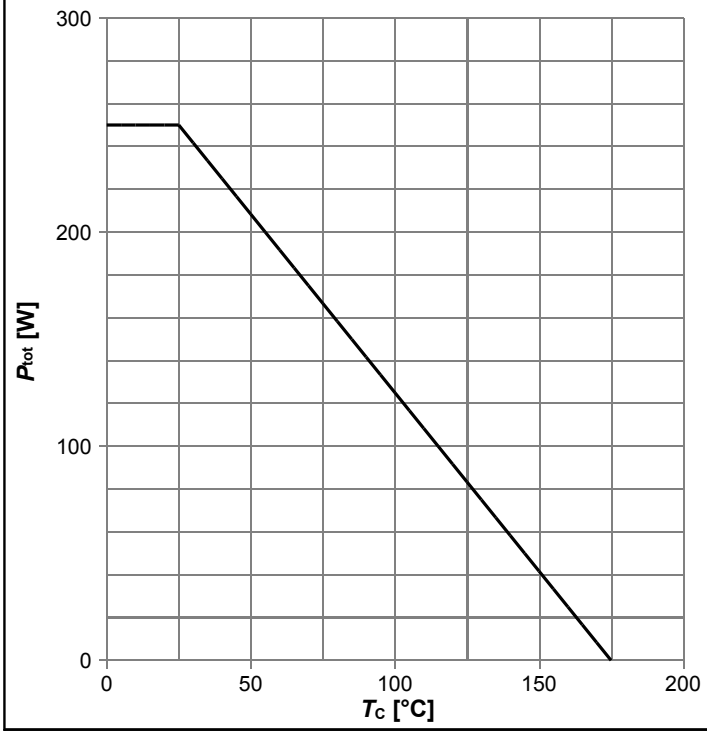
Table 7 Reverse diode

Parameter	Symbol	Values			Unit	Note / Test Condition
		Min.	Typ.	Max.		
Diode continous forward current	I_S	-	-	180	A	T_C=25 °C
Diode pulse current	$I_{S,pulse}$	-	-	884	A	T_C=25 °C
Diode forward voltage	V_{SD}	-	0.9	1.2	V	V_{GS}=0 V, I_F=90 A, T_j=25 °C
Reverse recovery time[1)]	t_{rr}	-	65	130	ns	V_R=50 V, I_F=*90*, di_F/dt=100 A/µs
Reverse recovery charge[1)]	Q_{rr}	-	123	246	nC	V_R=50 V, I_F=*90*, di_F/dt=100 A/µs

[1)] Defined by design. Not subject to production test.

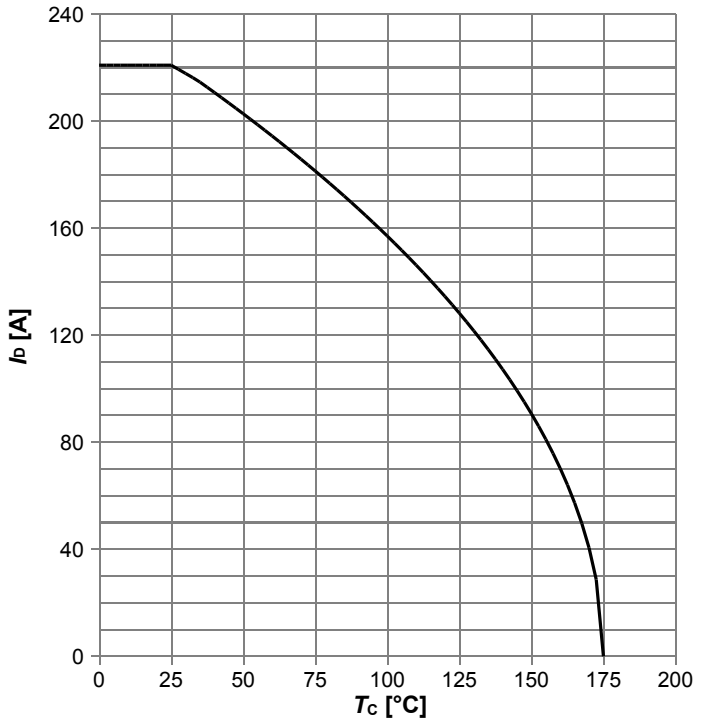
4 Electrical characteristics diagrams

Diagram 1: Power dissipation



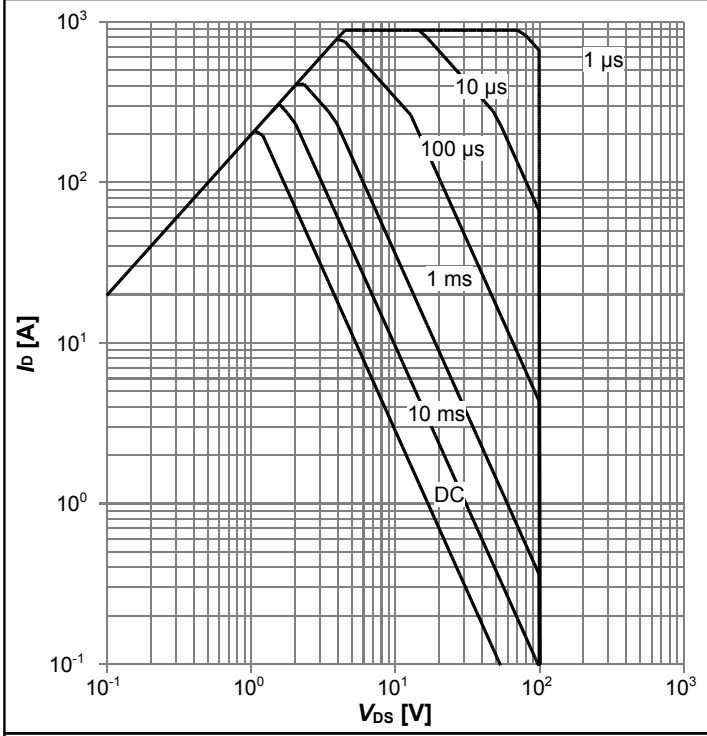
$P_{tot}=f(T_C)$

Diagram 2: Drain current



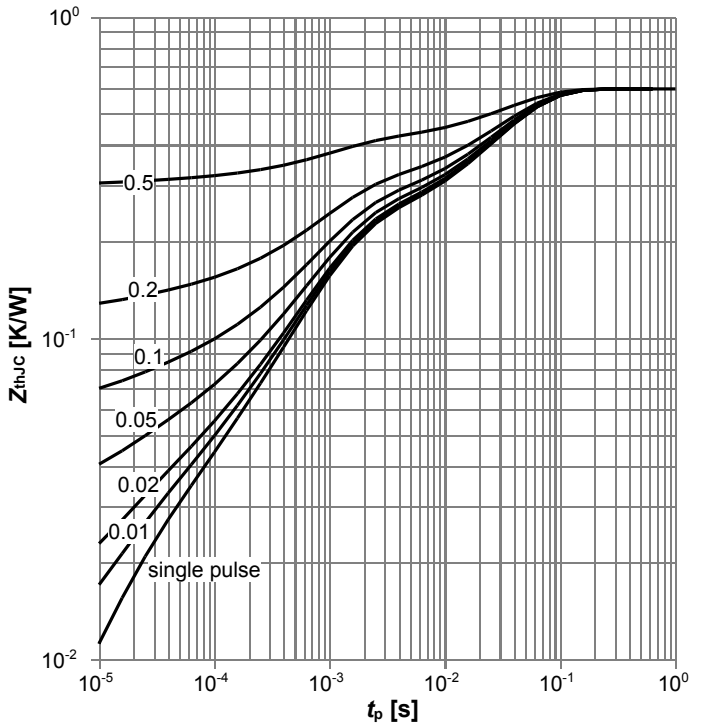
$I_D=f(T_C)$; $V_{GS}\geq 10$ V

Diagram 3: Safe operating area



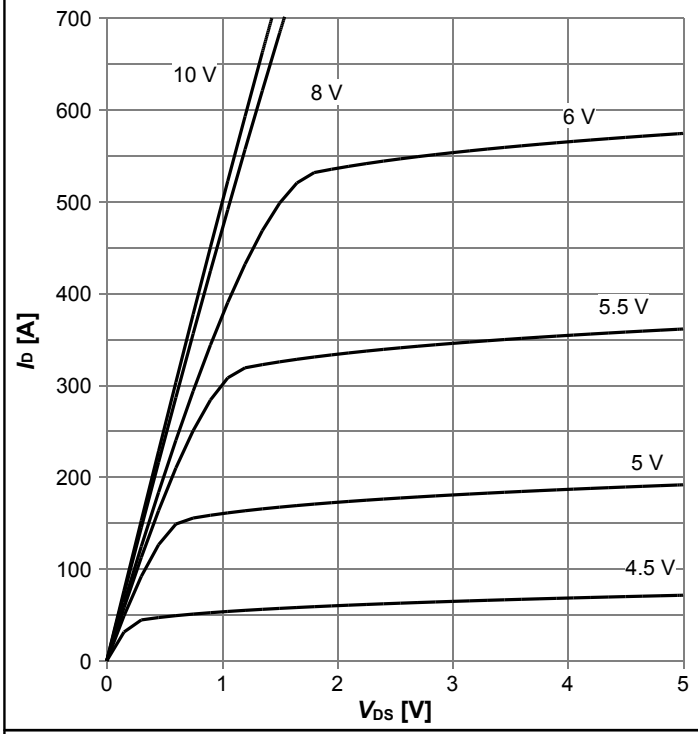
$I_D=f(V_{DS})$; $T_C=25$ °C; $D=0$; parameter: t_p

Diagram 4: Max. transient thermal impedance



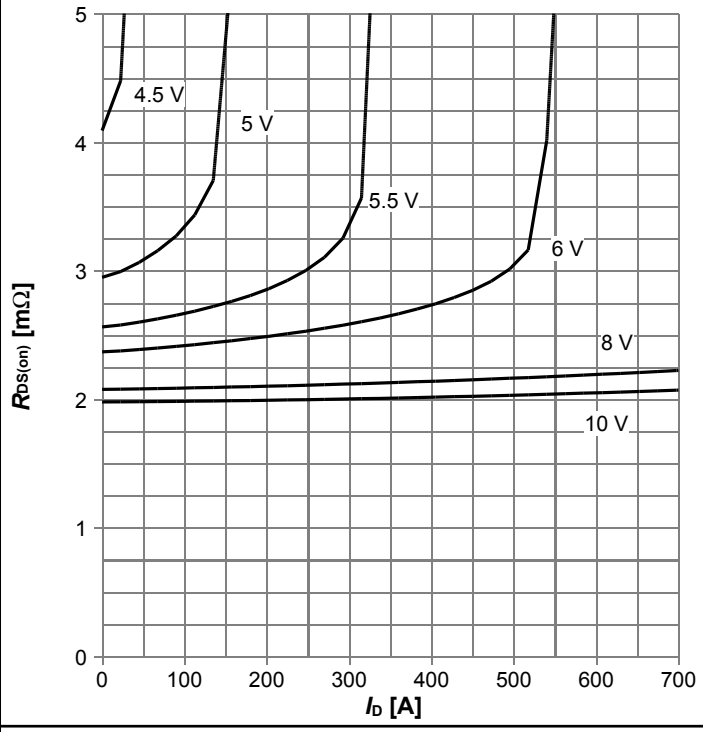
$Z_{thJC}=f(t_p)$; parameter: $D=t_p/T$

Diagram 5: Typ. output characteristics



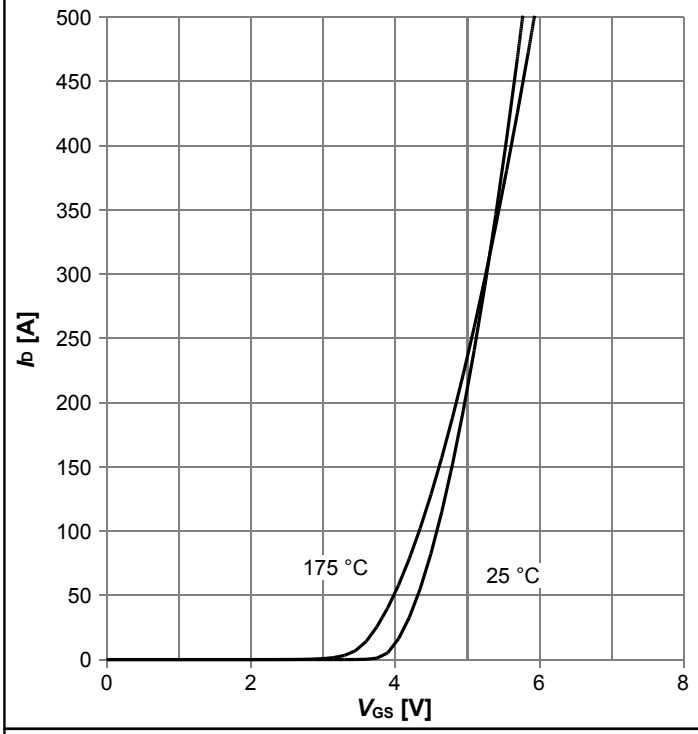
$I_D=f(V_{DS})$; $T_j=25$ °C; parameter: V_{GS}

Diagram 6: Typ. drain-source on resistance



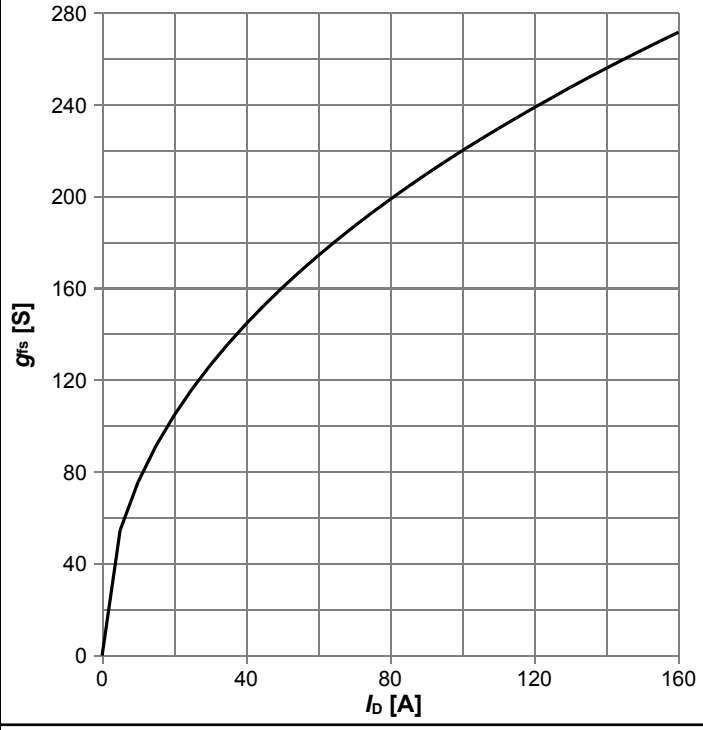
$R_{DS(on)}=f(I_D)$; $T_j=25$ °C; parameter: V_{GS}

Diagram 7: Typ. transfer characteristics



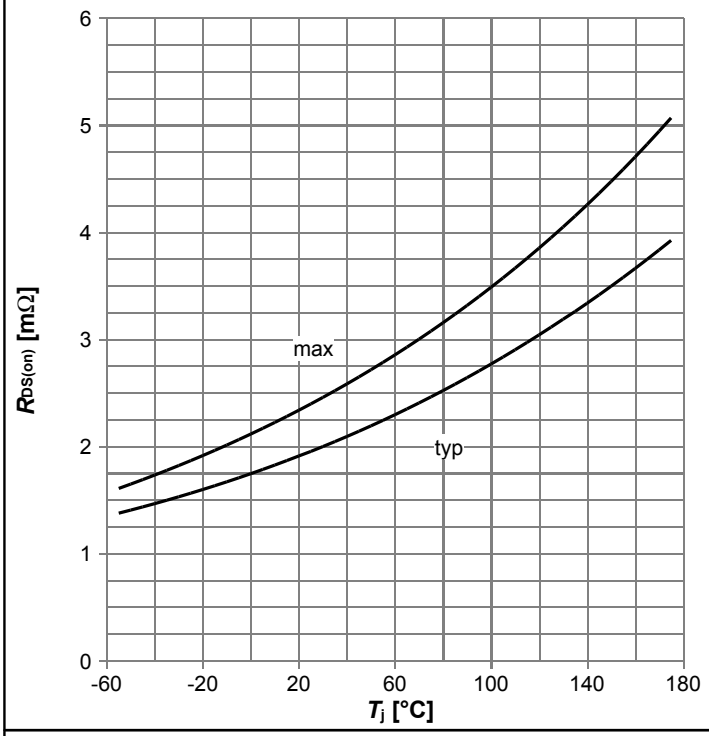
$I_D=f(V_{GS})$; $|V_{DS}|>2|I_D|R_{DS(on)max}$; parameter: T_j

Diagram 8: Typ. forward transconductance



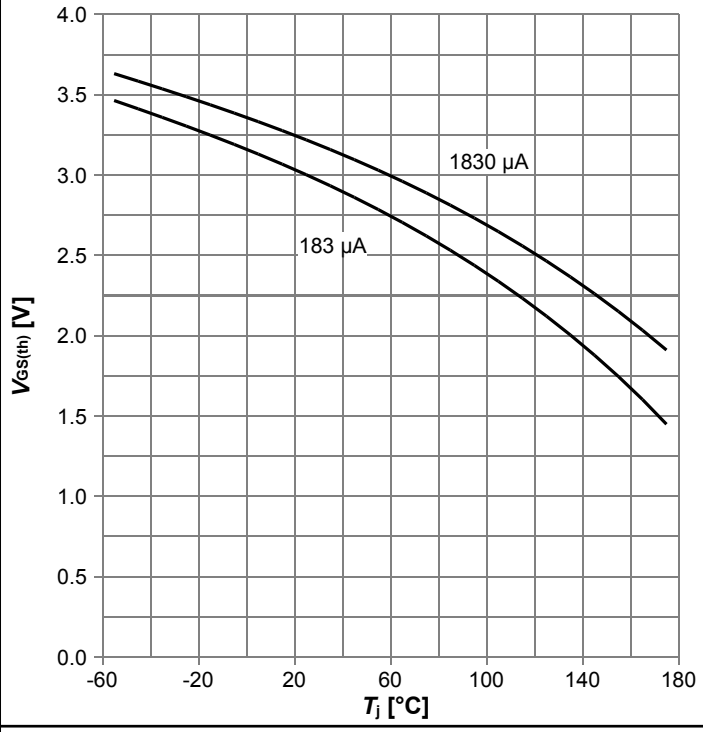
$g_{fs}=f(I_D)$; $T_j=25$ °C

Diagram 9: Drain-source on-state resistance



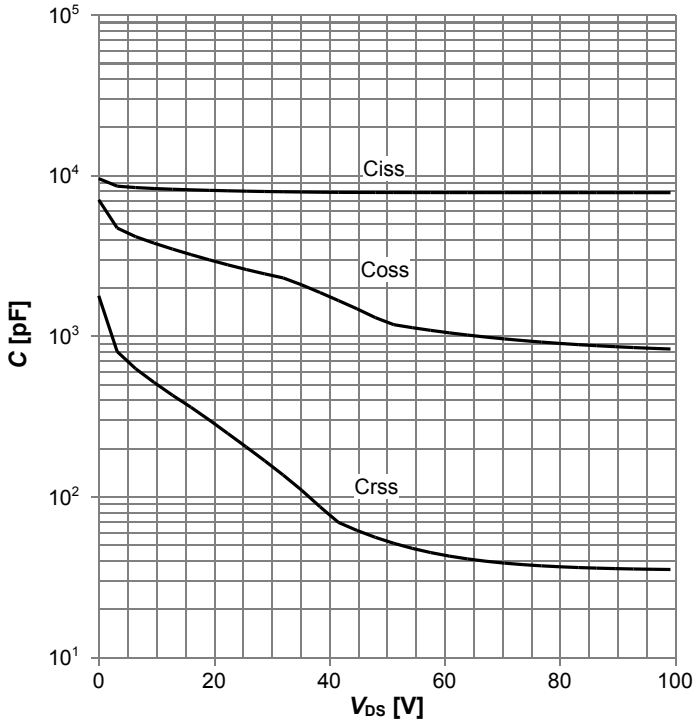
$R_{DS(on)}$=f(T_j); I_D=90 A; V_{GS}=10 V

Diagram 10: Typ. gate threshold voltage



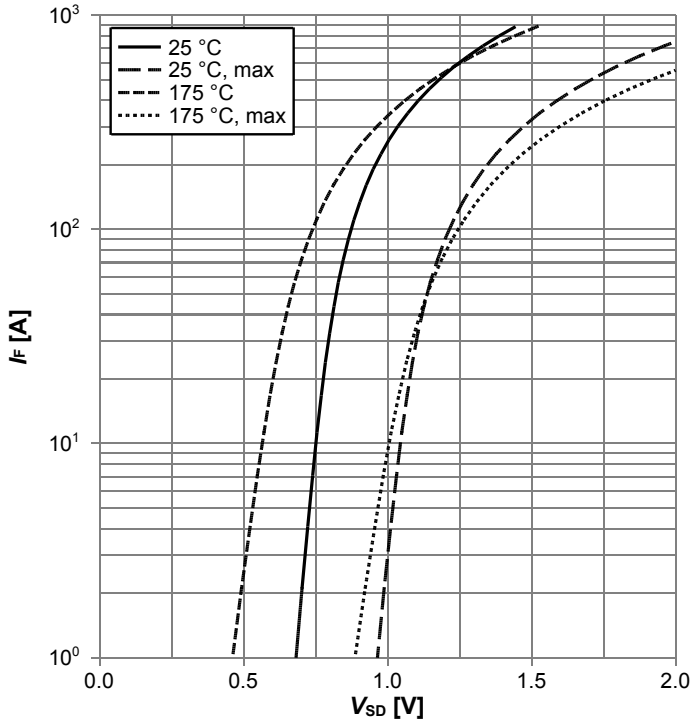
$V_{GS(th)}$=f(T_j); V_{GS}=V_{DS}; parameter: I_D

Diagram 11: Typ. capacitances



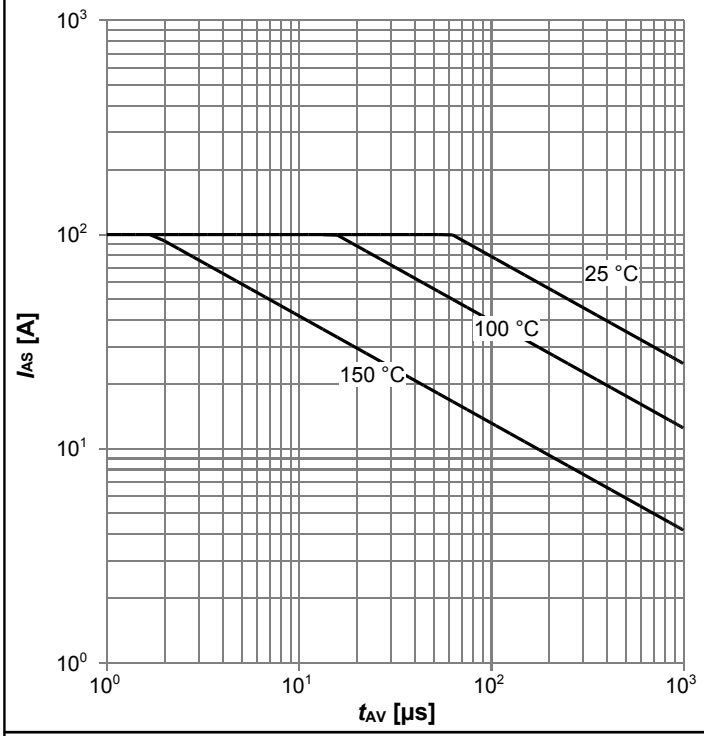
C=f(V_{DS}); V_{GS}=0 V; f=1 MHz

Diagram 12: Forward characteristics of reverse diode



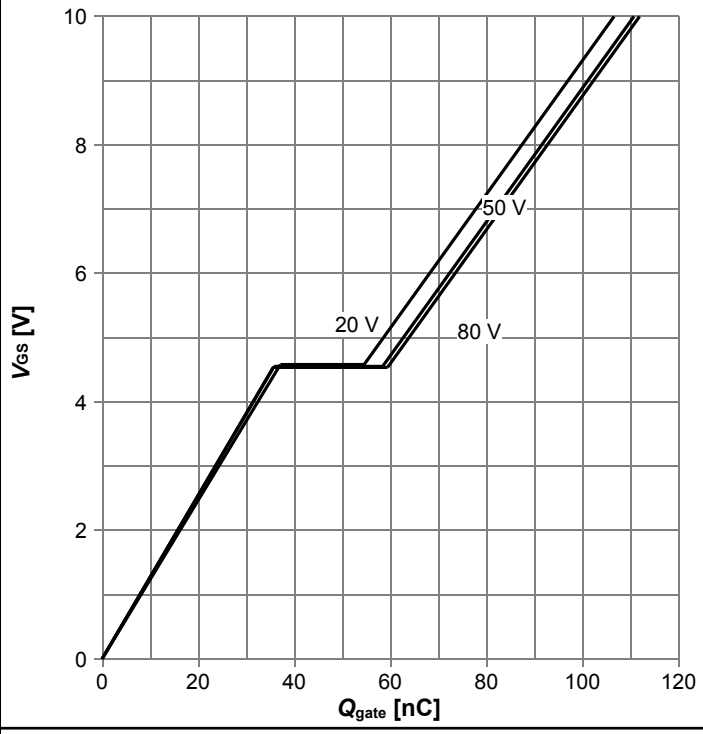
I_F=f(V_{SD}); parameter: T_j

Diagram 13: Avalanche characteristics



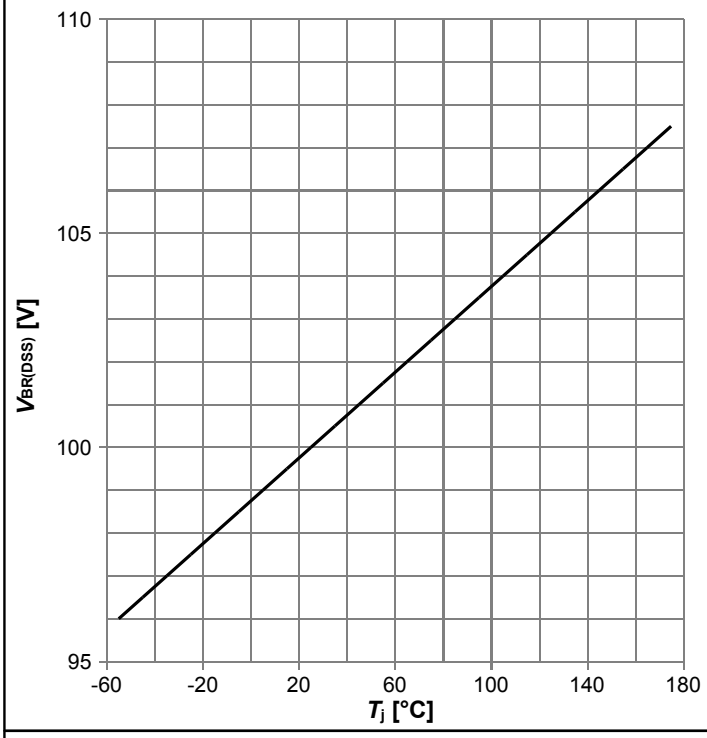
$I_{AS}=f(t_{AV})$; $R_{GS}=25\ \Omega$; parameter: $T_{j(start)}$

Diagram 14: Typ. gate charge



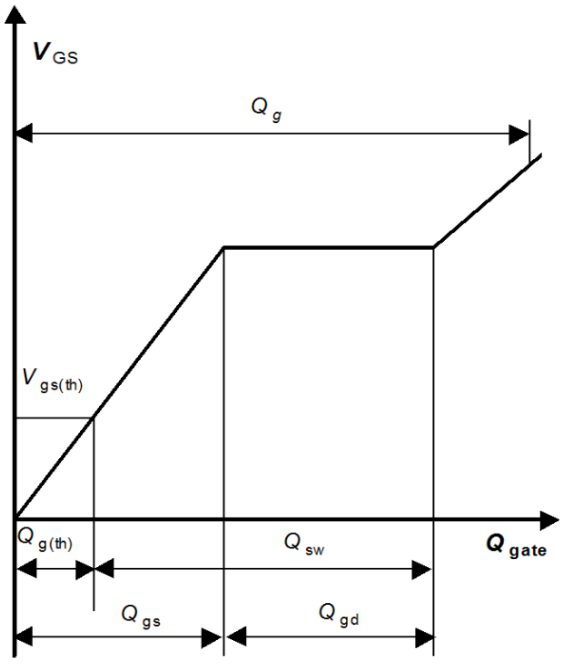
$V_{GS}=f(Q_{gate})$; $I_D=90$ A pulsed; parameter: V_{DD}

Diagram 15: Drain-source breakdown voltage

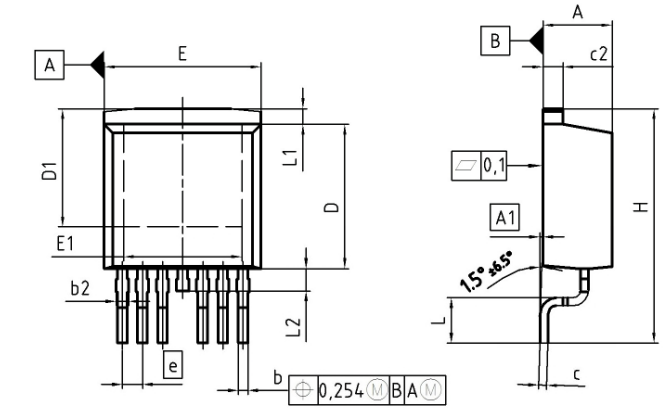


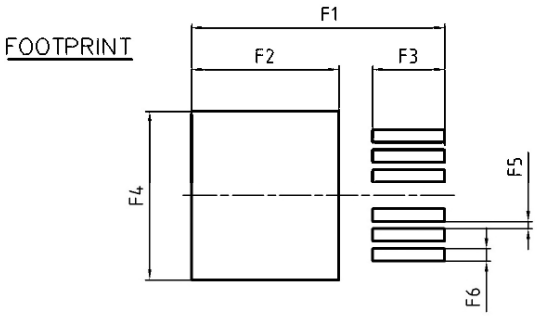
$V_{BR(DSS)}=f(T_j)$; $I_D=1$ mA

Diagram Gate charge waveforms



5 Package Outlines





DIM	MILLIMETERS		INCHES	
	MIN	MAX	MIN	MAX
A	4.30	4.57	0.169	0.180
A1	0.00	0.25	0.000	0.010
b	0.50	0.70	0.020	0.028
b2	0.50	1.00	0.020	0.039
c	0.33	0.65	0.013	0.026
c2	1.17	1.40	0.046	0.055
D	8.51	9.45	0.335	0.372
D1	6.90	7.90	0.272	0.311
E	9.80	10.31	0.386	0.406
E1	6.50	8.60	0.256	0.339
e	1.27		0.050	
N	6		6	
H	14.61	15.88	0.575	0.625
L	2.29	3.00	0.090	0.118
L1	0.70	1.60	0.028	0.063
L2	1.00	1.78	0.039	0.070
F1	16.05	16.25	0.632	0.640
F2	9.30	9.50	0.366	0.374
F3	4.50	4.70	0.177	0.185
F4	10.70	10.90	0.421	0.429
F5	0.37	0.57	0.015	0.022
F6	0.70	0.90	0.028	0.035

DOCUMENT NO.
Z8B00134765

SCALE
0 5 5
7.5mm

EUROPEAN PROJECTION

ISSUE DATE
05-11-2007

REVISION
01

Figure 1 Outline PG-TO263-7, dimensions in mm/inches

Revision History

IPB024N10N5

Revision: 2020-12-22, Rev. 2.2

Previous Revision		
Revision	Date	Subjects (major changes since last revision)
2.0	2016-04-11	Release of final version
2.1	2016-10-03	Update Avalanche Energy
2.2	2020-12-22	Update current rating

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